

# General purpose (dual digital transistors)

## EMH10 / UMH10N / IMH10A

### ●Features

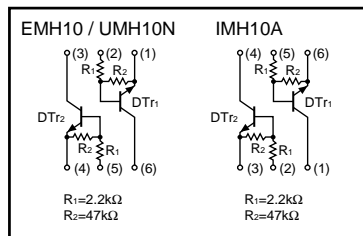
- 1) Two DTC123J chips in a EMT or UMT or SMT package.
- 2) Mounting possible with EMT3 or UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

### ●Structure

Epitaxial planar type  
NPN silicon transistor  
(Built-in resistor type)

The following characteristics apply to both DT<sub>r1</sub> and DT<sub>r2</sub>.

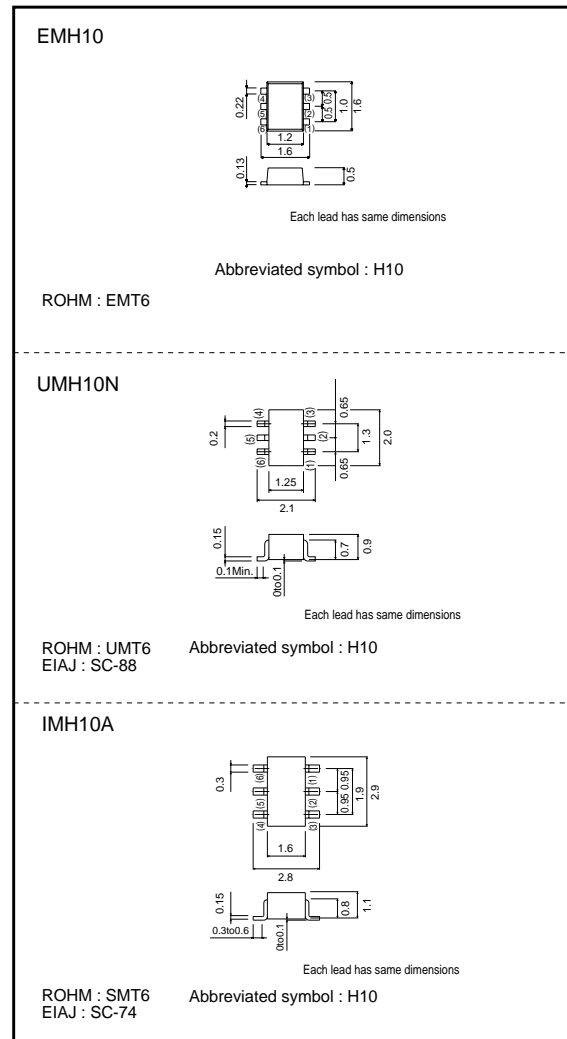
### ●Equivalent circuit



### ●Packaging specifications

| Type   | Package                      | Taping |      |      |
|--------|------------------------------|--------|------|------|
|        | Code                         | T2R    | TN   | T110 |
|        | Basic ordering unit (pieces) | 8000   | 3000 | 3000 |
| EMH10  |                              | ○      | -    | -    |
| UMH10N |                              | -      | ○    | -    |
| IMH10A |                              | -      | -    | ○    |

### ●External dimensions (Units : mm)



Transistors

●Absolute maximum ratings (Ta=25°C)

| Parameter           | Symbol                | Limits      | Unit |
|---------------------|-----------------------|-------------|------|
| Supply voltage      | V <sub>CC</sub>       | 50          | V    |
| Input voltage       | V <sub>IN</sub>       | 12          | V    |
|                     |                       | -5          |      |
| Output current      | I <sub>O</sub>        | 100         | mA   |
|                     | I <sub>C (Max.)</sub> | 100         | mA   |
| Power dissipation   | EMH10,UMH10N          | 150 (TOTAL) | mW   |
|                     | IMH10A                | 300 (TOTAL) |      |
| Storage temperature | T <sub>stg</sub>      | -55~+150    | °C   |

\*1 120mW per element must not be exceeded.  
 \*2 200mW per element must not be exceeded.

●Electrical characteristics (Ta=25°C)

| Parameter            | Symbol                         | Min. | Typ. | Max. | Unit | Conditions  |
|----------------------|--------------------------------|------|------|------|------|---|
| Input voltage        | V <sub>I (off)</sub>           | -    | -    | 0.5  | V    | V <sub>CC</sub> =5V, I <sub>O</sub> =100μA              |
|                      | V <sub>I (on)</sub>            | 1.1  | -    | -    |      | V <sub>O</sub> =0.3V, I <sub>O</sub> =5mA               |
| Output voltage       | V <sub>O (on)</sub>            | -    | 0.1  | 0.3  | V    | I <sub>O</sub> /I <sub>I</sub> =5mA/0.25mA              |
| Input current        | I <sub>I</sub>                 | -    | -    | 3.6  | mA   | V <sub>I</sub> =5V                                      |
| Output current       | I <sub>O (off)</sub>           | -    | -    | 0.5  | μA   | V <sub>CC</sub> =50V, V <sub>I</sub> =0V                |
| DC current gain      | G <sub>I</sub>                 | 80   | -    | -    | -    | V <sub>O</sub> =5V, I <sub>O</sub> =10mA                |
| Transition frequency | f <sub>T</sub>                 | -    | 250  | -    | MHz  | V <sub>CE</sub> =10mA, I <sub>E</sub> =-5mA, f=100MHz * |
| Input resistance     | R <sub>1</sub>                 | 1.54 | 2.2  | 2.86 | kΩ   | -   |
| Resistance ratio     | R <sub>2</sub> /R <sub>1</sub> | 17   | 21   | 26   | -    | -   |

\* Transition frequency of the device

●Electrical characteristic curves

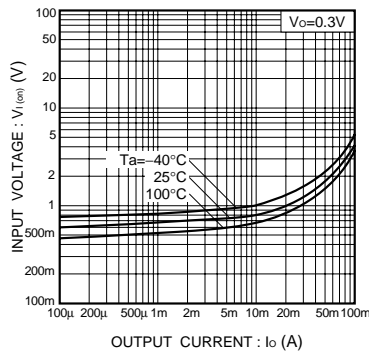


Fig.1 Input voltage vs. output current (ON characteristics)

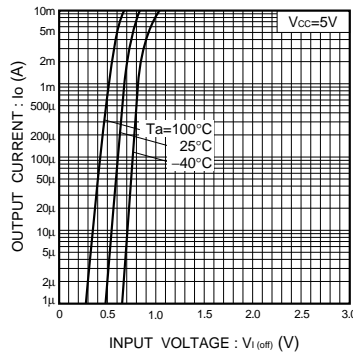


Fig.2 Output current vs. input voltage (OFF characteristics)

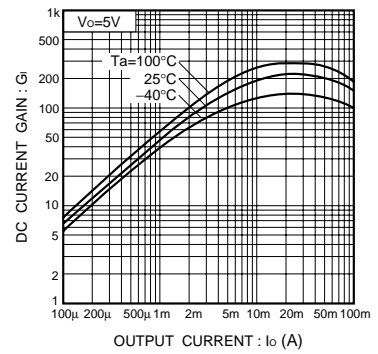


Fig.3 DC current gain vs. output current

Transistors

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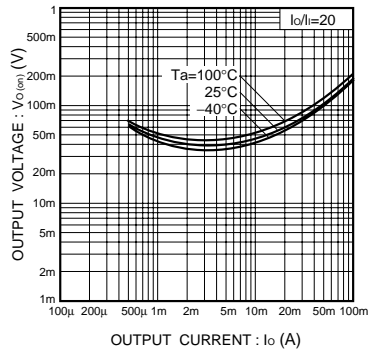


Fig.4 Output voltage vs. output current